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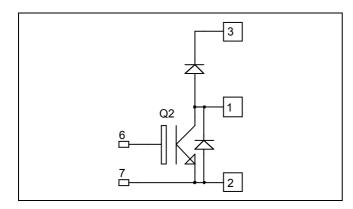




Boost chopper Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 600V$$

 $I_C = 400A$ @ $Tc = 80$ °C



Application

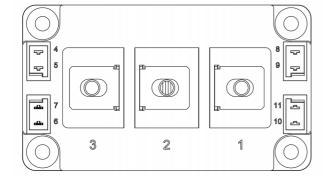
- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M6 power connectors

Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant



Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		600	V
Ţ	Continuous Collector Current	$T_C = 25^{\circ}C$	500	
$I_{\rm C}$	Continuous Conector Current	$T_C = 80$ °C	400	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	800	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	1250	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	800A @ 520V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$				500	μΑ
V _{CE(sat)}	Collector Emitter saturation Voltage		$T_j = 25$ °C		1.5	1.9	V
				1.7		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 6.4 \text{ mA}$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		24		
C_{oes}	Output Capacitance	$V_{CE} = 25V$		1.5		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz		0.75		
Q_{G}	Gate charge	V _{GE} =±15V, I _C =400A V _{CE} =300V		4.2		μС
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		110		ns
$T_{\rm r}$	Rise Time	$V_{GE} = \pm 15V$		50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$ $I_C = 400A$		490		
T_{f}	Fall Time	$R_G = 1.5\Omega$		50		
T _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C)		130		
T_{r}	Rise Time	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$		60		ns
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm C} = 400 A$		530		
T_{f}	Fall Time	$R_G = 1.5\Omega$		70		
Eon	Turn on Energy	$V_{GE} = \pm 15V$ $T_j = 25^{\circ}C$		3.2		
Lon	Turn on Energy	$V_{Bus} = 300V$ $T_{i} = 150^{\circ}C$		3.4		mJ
E_{off}	Turn off Energy	$I_C = 400A$ $T_j = 25^{\circ}C$		15		1110
2011		$R_G = 1.5\Omega$ $T_j = 150^{\circ}C$		15.5		
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bus} = 360V$ $t_p \le 6\mu s ; T_j = 150^{\circ}C$		2000		A

Reverse diode ratings and characteristics

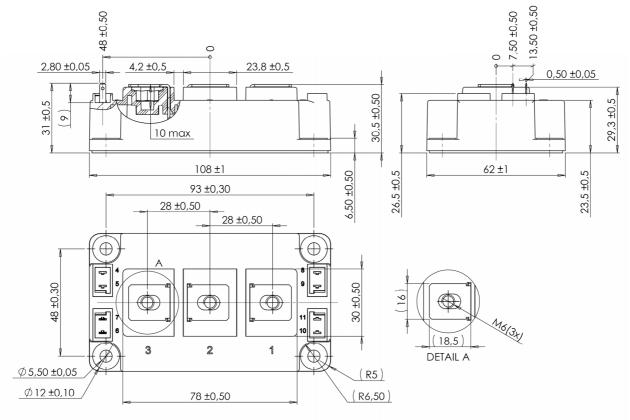
Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			600			V
I_{RRM}	Maximum Reverse Leakage Current	V _R =600V	$T_i = 25$ °C $T_i = 150$ °C			500 750	μА
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		400	730	A
V_{F}	Diode Forward Voltage	$I_F = 400A$ $V_{GE} = 0V$	$T_i = 25^{\circ}C$		1.6	2	V
v F			$T_{i} = 150^{\circ}C$		1.5		v
4	Reverse Recovery Time	$I_F = 400A$ $V_R = 300V$ $di/dt = 4800A/\mu s$	$T_j = 25^{\circ}C$		125		
t_{rr}			$T_{j} = 150^{\circ}C$		180		ns
0	Davanaa Daaayami Chanaa		$T_j = 25^{\circ}C$		18.8		C
Q_{rr}	Reverse Recovery Charge		$T_i = 150^{\circ}C$		39.5		μC
E_{rr}	Reverse Recovery Energy	αι/αι 1000/1/μ3	$T_i = 25^{\circ}C$		4.4		Т
			$T_{\rm j} = 150^{\circ}{\rm C}$		9.6		mJ



Thermal and package characteristics

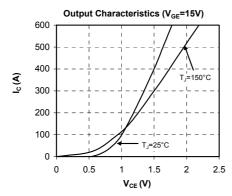
Symbol	Characteristic			Min	Тур	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.12	°C/W
1\(\text{thJC}\)			Diode			0.20	C/ VV
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range Storage Temperature Range			-40		175	
T_{STG}			-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque -	For terminals	M6	3		5	N.m
		To Heatsink	M6	3		5	18.111
Wt	Package Weight					350	g

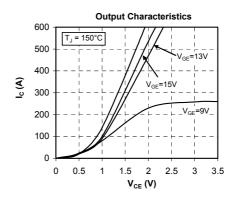
D3 Package outline (dimensions in mm)

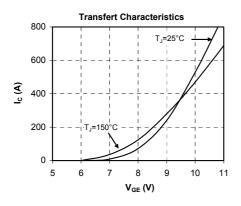


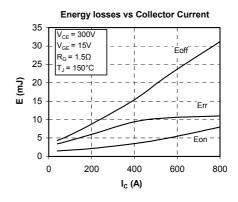


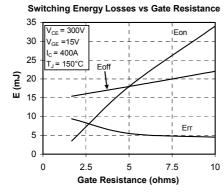
Typical Performance Curve

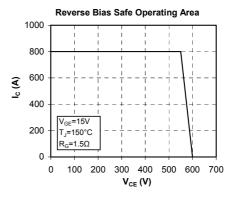


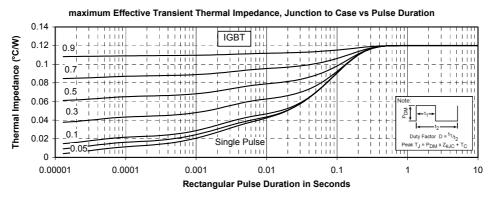




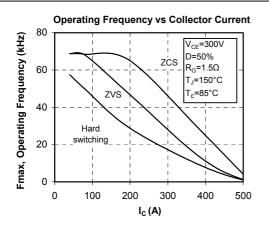


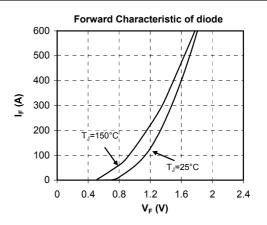


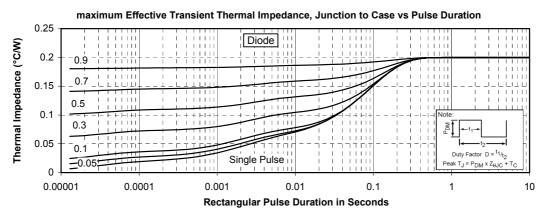












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